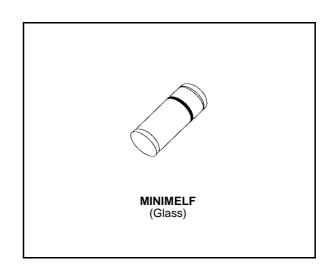


SMALL SIGNAL SCHOTTKY DIODES



DESCRIPTION

General purpose, metal to silicon diodes featuring very low turn-on voltage fast switching.

These devices have integrated protection against excessive voltage such as electrostatic discharges.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	30	V
l _F	Forward Continuous Current	200	mA
I _{FRM}	Repetitive Peak Fordware Current	500	mA
I _{FSM}	Surge non Repetitive Forward Current	4	Α
P _{tot}	Power Dissipation	200	mW
$T_{stg} \ T_{j}$	Storage and Junction Temperature Range	- 65 to 150 - 65 to 125	°C
TL	Maximum Temperature for Soldering during 1	260	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-l)}$	Junction-leads	300	°C/W

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ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol		Min.	Тур.	Max.	Unit		
V_{BR}	T _j = 25°C	$I_R = 100 \mu A$		30			V
V _F *	T _j = 25°C	$I_F = 200 \text{mA}$	All Types			1	V
	T _j = 25°C	$I_F = 10mA$	BAT 42			0.4	
	T _j = 25°C	$I_F = 50 \text{mA}$				0.65	
	T _j = 25°C	$I_F = 2mA$	BAT 43	0.26		0.33	
	T _j = 25°C	I _F = 15mA				0.45	
I _R *	T _j = 25°C		V _R = 25V			0.5	μΑ
	T _j = 100°C					100	

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions	Min.	Тур.	Max.	Unit
С	$T_j = 25$ °C $V_R = 1$ V $f = 1$ MHz		7		pF
trr	$T_{j} = 25^{\circ}C$ $I_{F} = 10$ mA $I_{R} = 10$ mA $I_{rr} = 1$ mA $R_{L} = 100\Omega$			5	ns
η	$T_j = 25$ °C $R_L = 15$ K Ω $C_L = 300$ pF $f = 45$ MHz $V_i = 2$ V	80			%

^{*} Pulse test: $t_p \le 300 \mu s$ $\delta < 2\%$.

Figure 1. Forward current versus forward voltage at different temperatures (typical values).

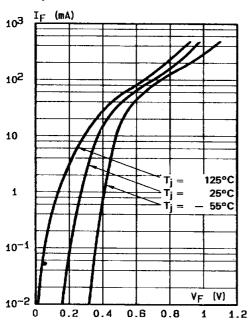
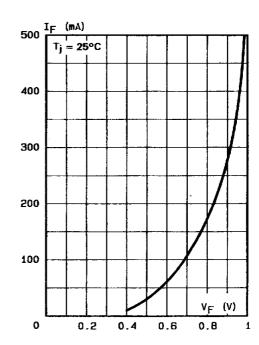


Figure 2. Forward current versus forward voltage (typical values).



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Figure 3. Reverse current versus junction temperature.

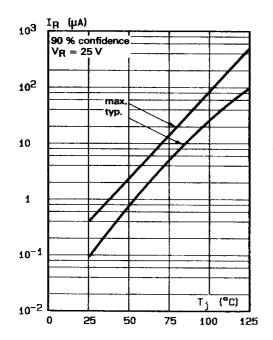


Figure 4. Reverse current versus continuous reverse voltage (typical values).

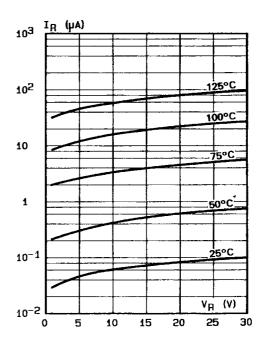
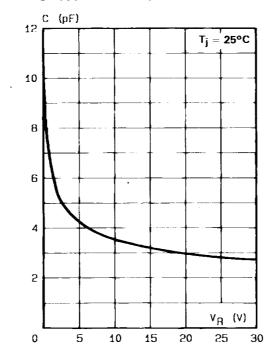
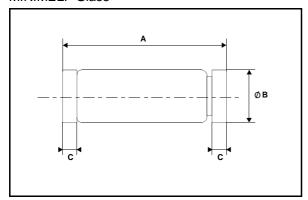


Figure 5. Forward current versus forward voltage (typical values).



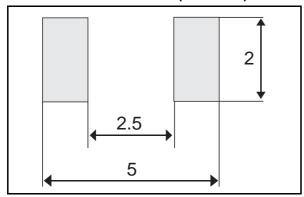
PACKAGE MECHANICAL DATA

MINIMELF Glass



			DIMEN	SIONS		
REF.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
Α	3.30	3.40	3.6	0.130	0.134	0.142
В	1.59	1.60	1.62	0.063	0.063	0.064
С	0.40	0.45	0.50	0.016	0.018	0.020
D		1.50			0.059	

FOOT PRINT DIMENSIONS (Millimeter)



Marking: ring at cathode end. Weight: 0.05g

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